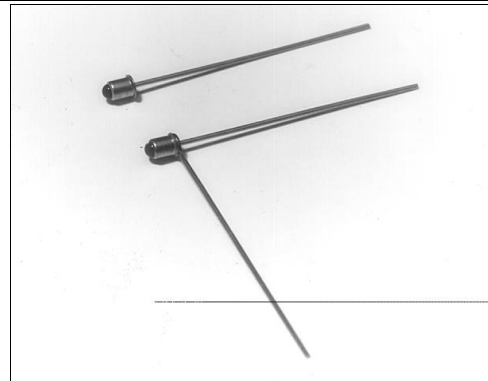


SD1440

Silicon Phototransistor

FEATURES

- Compact, metal can coaxial package
- 24° (nominal) acceptance angle
- Wide sensitivity ranges
- Wide operating temperature range (- 55°C to +125°C)
- Mechanically and spectrally matched to SE1450 and SE1470 infrared emitting diodes



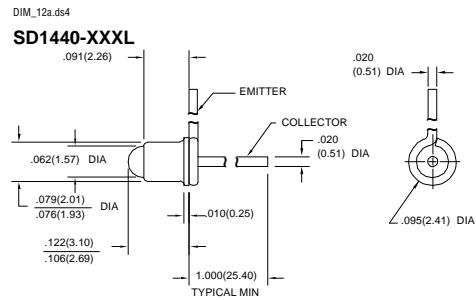
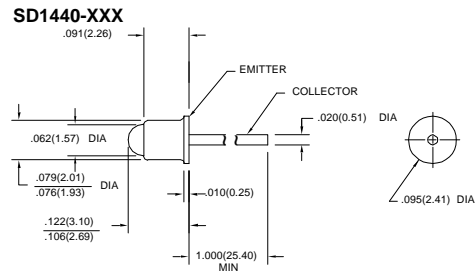
INFRA-63.TIF

DESCRIPTION

The SD1440 is an NPN silicon phototransistor mounted in a glass lensed metal can coaxial package. The package may have a tab or second lead welded to the can as an optional feature (SD1440-XXXL). Both leads are flexible and may be formed to fit various mounting configurations.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals ±0.005(0.12)
2 plc decimals ±0.020(0.51)



DIM_12b.ds4

SD1440

Silicon Phototransistor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current SD1440-001, SD1440-001 L SD1440-002, SD1440-002 L SD1440-003, SD1440-003 L SD1440-004, SD1440-004 L	I_L	0.7 1.5 3.0 6.0			mA	$V_{CE}=5\text{ V}$ $H=5\text{ mW/cm}^2$ (1)
Collector Dark Current	I_{CEO}			100	nA	$V_{CE}=10\text{ V}$, $H=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_C=100\text{ }\mu\text{A}$
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5.0			V	$I_E=100\text{ }\mu\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$			0.4	V	$I_C=0.4\text{ mA}$ $H=5\text{ mW/cm}^2$
Angular Response (2)	\emptyset		24		degr.	$I_F=\text{Constant}$
Rise And Fall Time	t_r, t_f		15		μs	$V_{CC}=5\text{ V}$, $I_L=1\text{ mA}$ $R_L=1000\text{ }\Omega$

Notes

- The radiation source is a tungsten lamp operating at a color temperature of 2870°K.
- Angular response is defined as the total included angle between the half sensitivity points.

ABSOLUTE MAXIMUM RATINGS

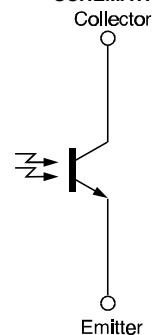
(25°C Free-Air Temperature unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	75 mW (1)
Operating Temperature Range	-55°C to 125°C
Storage Temperature Range	-65°C to 150°C
Soldering Temperature (10 sec)	260°C

Notes

- Derate linearly from 25°C free-air temperature at the rate of 0.71 mW/°C.

SCHEMATIC



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

Honeywell

SD1440

Silicon Phototransistor

SWITCHING TIME TEST CIRCUIT

cir_015.cdr

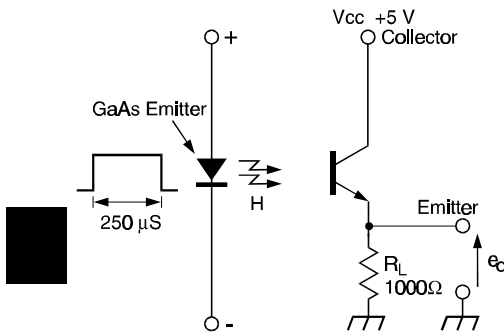


Fig. 1 Responsivity vs Angular Displacement

gra_051.ds4

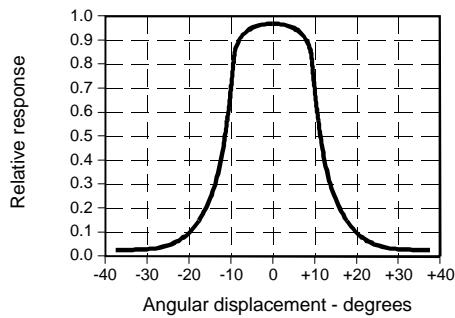
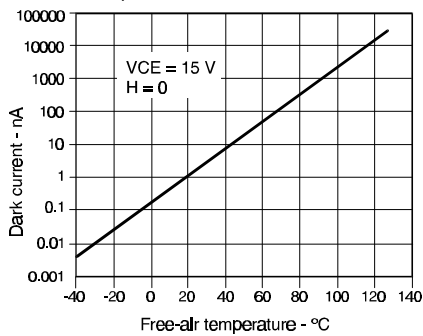


Fig. 3 Dark Current vs Temperature

gra_303.cdr



SWITCHING WAVEFORM

cir_004.cdr

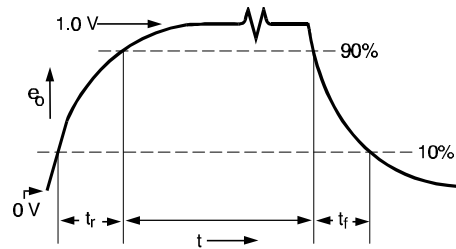


Fig. 2 Collector Current vs Ambient Temperature

gra_039.ds4

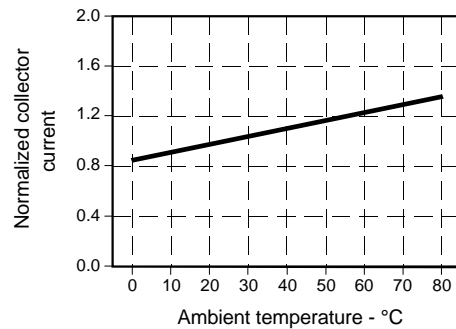
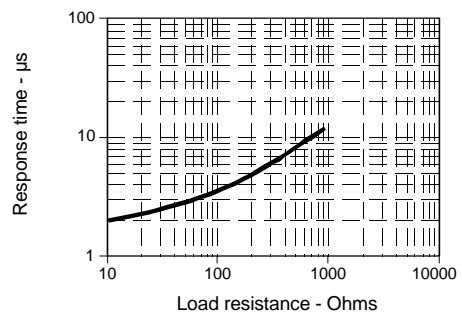


Fig. 4 Non-Saturated Switching Time vs Load Resistance

gra_041.ds4



SD1440

Silicon Phototransistor

Fig. 5 Spectral Responsivity

gra_036.ds4

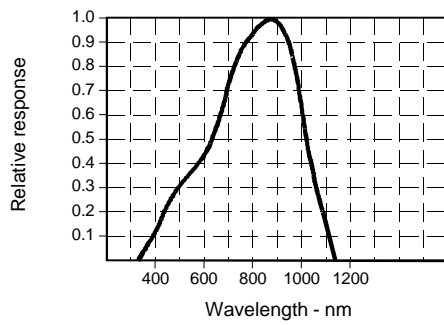
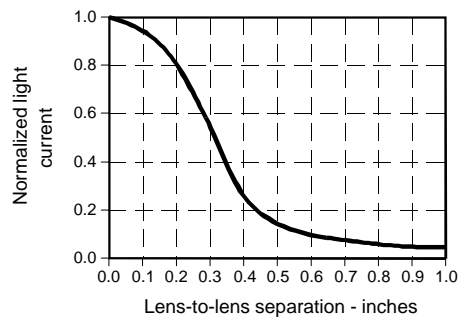


Fig. 6 Coupling Characteristics with SE1450

gra_006.ds4



All Performance Curves Show Typical Values